PROCESS FOR FABRICATING A SEMICONDUCTOR STRUCTURE EMPLOYING A TEMPORARY BOND

ABSTRACT

The invention relates to a process for fabricating a semiconductor structure, characterized in that it comprises the following steps: providing (E1) a handle substrate (1, 2) comprising a seed substrate (1) and a weakened sacrificial layer (2) covering the seed substrate (1); joining (E2) the handle substrate (1, 2) with a carrier substrate (3); optionally treating (E3) the carrier substrate (3); detaching (E4) the handle substrate at the sacrificial layer (2) so as to form the semiconductor structure; and removing (E5) any residue of the sacrificial layer (2) present on the seed substrate (1).

Fig. 3